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CONFIRMATION NO. 2556

<b>SERIAL NUMBER</b> 10/765,502	<b>FILING OR 371(c) DATE</b> 01/28/2004 <b>RULE</b>	<b>CLASS</b> 117	<b>GROUP ART UNIT</b> 1722	<b>ATTORNEY DOCKET NO.</b> R2184.0282/P282
<b>APPLICANTS</b> Hirokazu Iwata, Miyagi, JAPAN; Seiji Sarayama, Miyagi, JAPAN; Hisanori Yamane, Miyagi, JAPAN; Masahiko Shimada, Miyagi, JAPAN; Masato Aoki, Miyagi, JAPAN;				
<b>** CONTINUING DATA *****</b>				
<b>** FOREIGN APPLICATIONS *****</b> JAPAN 2003-019716 01/29/2003 JAPAN 2003-071302 03/17/2003 JAPAN 2003-081836 03/25/2003 JAPAN 2004-011536 01/20/2004 JAPAN 2004-012906 01/21/2004 JAPAN 2004-013562 01/21/2004				
<b>IF REQUIRED, FOREIGN FILING LICENSE GRANTED</b> <b>** 06/15/2004</b>				
Foreign Priority claimed <input checked="" type="checkbox"/> yes <input checked="" type="checkbox"/> no 35 USC 119 (a-d) conditions <input checked="" type="checkbox"/> yes <input checked="" type="checkbox"/> no <input type="checkbox"/> Met after met Allowance		<b>STATE OR COUNTRY</b> JAPAN	<b>SHEETS DRAWING</b> 19	<b>TOTAL CLAIMS</b> 49
Verified and Acknowledged Examiner's Signature _____ Initials _____		<b>INDEPENDENT CLAIMS</b> 14		
<b>ADDRESS</b> 24998				
<b>TITLE</b> Method of growing group III nitride crystal, group III nitride crystal grown thereby, group III nitride crystal growing apparatus and semiconductor device				
<b>FILING FEE RECEIVED</b> 2748	FEES: Authority has been given in Paper No. _____ to charge/credit DEPOSIT ACCOUNT No. _____ for following:		<input type="checkbox"/> All Fees <input type="checkbox"/> 1.16 Fees ( Filing ) <input type="checkbox"/> 1.17 Fees ( Processing Ext. of time ) <input type="checkbox"/> 1.18 Fees ( Issue ) <input type="checkbox"/> Other _____ <input type="checkbox"/> Credit	